



Resonant inelastic x-ray scattering: probing chemical bonding in transition metal compounds

Research supervisor: Cormac McGuinness
X-ray Spectroscopy Group

Scientific Background / Current Research

The nature of the chemical bond is of fundamental interest as it is the interplay between the physical structure and chemical bonding in a material which gives rise to the electronic bandstructure and the properties. Photon-in/photon-out **x-ray absorption/emission spectroscopy** or **resonant inelastic x-ray scattering**, is elementally selective and can probe either end of a metal-anion chemical bond in a transition metal fluoride or oxide binary compound, impossible by any other method. This can be exploited in e.g. MnF_2 a rutile transition metal fluoride and prototypical antiferromagnet, as well as other MA_2 systems in which the anion (oxygen or fluorine) is sp^2 hybridised such as in TiO_2 (rutile or anatase). In these due to the anisotropy of the chemical bonding and crystal structure, there is a combination of polarisation dependence (**dichroism**) and **symmetry-** and **state-selectivity** in the observed RIXS/RXES e.g. at the fluorine K edge. This dichroism gives separate probes of the differing occupied σ -like and π -like Metal-Anion-derived orbitals that contribute to the electronic bandstructure in these systems. Measurements at an elementally selective metal L-edge then gives complementary information from the other side of the Metal-Anion chemical bond.

Project

To measure the **symmetry dependent resonant x-ray emission spectroscopy** or **resonant inelastic x-ray scattering** for a variety of structurally similar transition metal fluorides and oxide. We seek to **measure** and **model** this polarisation dependent RXES at the anion K-edge and especially in metal 2p-3d RIXS and observe in detail how this varies with d-shell filling across the transition metal period. We will connect this with **models** of the electronic bandstructure to **derive further insight** into chemical bonding in these materials. These measurements and derived model spectra will in particular be applied to defective TiO_2 , *as used in memristors*, to probe the **local defective electronic structure** due to anion (oxygen) vacancies and cation (or Ti^{3+}) interstitials. Bulk single crystal samples of these materials are available and epitaxial thin films will be grown. RXES/RIXS measurements take place at **synchrotron radiation** facilities, such as those at MAXLAB in Sweden, the Swiss Light Source or Advanced Light Source (ALS), Lawrence Berkeley Lab, CA USA.

MAXLAB

ALS

International synchrotron radiation facilities: MAXLAB in Lund, Sweden, and the Advanced Light Source at Lawrence Berkeley Laboratory, California.

Also shown is an x-ray emission spectrometer

Example: TiO_2 - anatase

X-rays

σ RXES

π RXES

O - sp^2 hybridisation

Overview of typical measurements

Contact details – Cormac.McGuinness@tcd.ie

Room no: SNIAM 3.17; tel. +353 1 896 3547

<http://www.tcd.ie/Physics/People/Cormac.McGuinness/Research/>

Funding

Funding may be possible under HEA PRTL1 5 programme

More information / References